风光欣技术资料

TIP42C

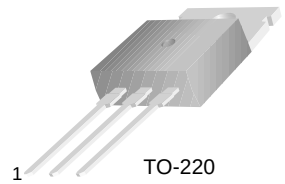
—PNP silicon —

■■**APPLICATION：AMPLIFIER APPLICATION,**

AWITCHING APPLICATION.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-100	V
Collector-emitter voltage	V_{CEO}	-100	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-6	A
Base current	I_B	-3	A
Collector Power Dissipation (Ta=25℃)	P_C	2	W
Collector Power Dissipation (Tc=25℃)	P_C	65	W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	- 65~150	℃



1.Base 2.Collector 3.Emitter

■■**ELECTRICALCHARACTERISTICSX**

（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE1}	15		75		V_{CE}= -4V，Ic= -3A
	h_{FE2}	30				V_{CE}= -4V，Ic= -0.3A
Collector-Emitter Cut-off Current	I_{CEO}			-0.7	mA	V_{CE}=-60V，I_E=0
Emitter-Base Cut-off Current	I_{EBO}			-1	mA	V_{EB}=-5V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	-100			V	Ic= -1mA，I_E=0
Base-Emitter on Voltage	BV_{CEO}	-100			V	Ic= -30mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	I_E= -1mA，Ic=0
Base-Emitter on Voltage	V_{BE}			-2	V	V_{CE}= -4V，Ic= -6A
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-1.5	V	Ic= -6A，I_B=-0.6A
Gain bandwidth product	f_T	3			MHz	V_{CE}=-10V,Ic=-0.5A,f =1MHz

■■hFE **Classification And Marking**

Print Mark	
Classification	
h_{FE}	15~75